

Shin-ichiro Gozu

List of Publications by Year in descending order

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times ranked

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| # | ARTICLE | IF | CITATIONS |
|----|--|-----|-----------|
| 1 | Highly strained InAlP/InGaAs-based coupled double quantum wells on InP substrates. Japanese Journal of Applied Physics, 2018, 57, 055501. | 1.5 | 0 |
| 2 | Residual electric fields of InGaAs/AlAs/AlAsSb (001) coupled double quantum wells structures assessed by photoreflectance anisotropy. International Journal of Modern Physics B, 2016, 30, 1550248. | 2.0 | 2 |
| 3 | Crystal quality of InGaAs/AlAs/InAlAs coupled double quantum wells for intersubband transition devices. Journal of Crystal Growth, 2015, 425, 102-105. | 1.5 | 9 |
| 4 | All-optical XOR logic gate using intersubband transition in III-V quantum well materials. Optics Express, 2014, 22, 12861. | 3.4 | 3 |
| 5 | Bandgap Control for Intersubband Transition in InGaAs/AlAsSb Coupled Double Quantum Wells. IEEE Photonics Technology Letters, 2013, 25, 1474-1477. | 2.5 | 1 |
| 6 | InGaAs/AlAs/InAlAs coupled double quantum wells for intersubband transition devices operating at 1550nm. Journal of Crystal Growth, 2013, 378, 134-136. | 1.5 | 7 |
| 7 | Band edge tailoring of InGaAs/AlAsSb coupled double quantum wells for a monolithically integrated all-optical switch. Optics Express, 2013, 21, 15840. | 3.4 | 14 |
| 8 | Optical and structural properties of In _{0.64} Ga _{0.36} As ⁺ Al _x Ga _{1-x} As(x=0.2) ⁺ AlAsSb coupled double quantum wells. , 2013, , . | | 0 |
| 9 | Picosecond Carrier Spin Relaxation in In _{0.8} Ga _{0.2} As/AlAs/AlAs _{0.56} Sb _{0.44} Coupled Double Quantum Wells. Japanese Journal of Applied Physics, 2013, 52, 04CM05. | 1.5 | 0 |
| 10 | Intersubband All-Optical Switch with Bandgap Control of InGaAs/AlAsSb Quantum Wells. , 2013, , . | | 0 |
| 11 | Exciton spin relaxation in In _{0.53} Ga _{0.47} As/AlAs _{0.56} Sb _{0.44} quantum wells. Applied Physics Letters, 2012, 100, 092401. | 3.3 | 1 |
| 12 | Ultrafast all-optical switch with cross-phase modulation by area-selective ion implantation in InGaAs/AlAsSb coupled double quantum wells. Optics Express, 2012, 20, B279. | 3.4 | 8 |
| 13 | Effects of shutter transients in molecular beam epitaxy. Nanoscale Research Letters, 2012, 7, 620. | 5.7 | 4 |
| 14 | Photoreflectance study of InGaAs/AlAsSb coupled double quantum wells. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 334-337. | 0.8 | 2 |
| 15 | Monolithically Integrated Intersubband All-Optical Switch using Area-Selective Activation of Cross-Phase Modulation in InGaAs/AlAsSb Quantum Wells. , 2012, , . | | 0 |
| 16 | Study of the shrinkage caused by holographic grating formation in acrylamide based photopolymer film. Optics Express, 2011, 19, 13386. | 3.4 | 16 |
| 17 | Carrier spin relaxation in InGaAs ⁺ AlAsSb quantum wells. , 2011, , . | | 0 |
| 18 | Surface photovoltage and photoreflectance study of InGaAs ⁺ AlAsSb quantum wells. , 2011, , . | | 0 |

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|----|---|-----|-----------|
| 19 | Strain control of InGaAs/AlAs/AlAsSb quantum wells by interface termination method between AlAs and AlAsSb. <i>Journal of Crystal Growth</i> , 2011, 323, 39-41. | 1.5 | 2 |
| 20 | Ultrafast electron dynamics of intersubband excitation concerning cross-phase modulation in an InGaAs/AlAs/AlAsSb coupled double quantum well. <i>Applied Physics Letters</i> , 2011, 98, 251104. | 3.3 | 6 |
| 21 | Four-wave mixing in InGaAs/AlAsSb intersubband transition optical waveguides. <i>Journal of Applied Physics</i> , 2011, 110, . | 2.5 | 2 |
| 22 | Refractive index of high-carrier-doped InGaAs/AlAsSb coupled double quantum wells. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2010, 42, 2661-2664. | 2.7 | 0 |
| 23 | Simultaneous generation of intersubband absorption and quantum well intermixing through silicon ion implantation in undoped InGaAs/AlAsSb coupled double quantum wells. <i>Applied Physics Letters</i> , 2010, 96, 101901. | 3.3 | 8 |
| 24 | All-optical wavelength conversion at 40Gb/s with enhanced XPM by facet reflection using intersubband transition in InGaAs/AlAsSb quantum well waveguide. , 2010, , . | | 1 |
| 25 | Molecular beam epitaxy and characterization of InGaAs ⁺ /AlAs ⁺ /AlAsSb coupled double quantum wells with extremely thin coupling barriers. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2010, 28, C3C25-C3C28. | 1.2 | 3 |
| 26 | Observation of Spin Relaxation in InGaAs/AlAsSb Quantum Wells. <i>Japanese Journal of Applied Physics</i> , 2010, 49, 04DM03. | 1.5 | 1 |
| 27 | All-Optical Cross-Phase Modulation Generation by Ion Implantation in III-V Quantum Wells. <i>IEEE Photonics Technology Letters</i> , 2010, 22, 1820-1822. | 2.5 | 5 |
| 28 | Molecular beam epitaxy of AlAsSb/AlAs/InGaAs coupled double quantum wells with extremely thin AlAs center barrier. <i>Journal of Crystal Growth</i> , 2009, 311, 1700-1702. | 1.5 | 5 |
| 29 | High-resolution X-ray diffraction analysis of InGaAs/AlAsSb coupled double quantum wells grown by molecular beam epitaxy. <i>Journal of Crystal Growth</i> , 2009, 311, 1707-1710. | 1.5 | 1 |
| 30 | Experimental and theoretical study of cross-phase modulation in InGaAs/AlAsSb coupled double quantum wells with a AlGaAs coupling barrier. <i>Physical Review B</i> , 2009, 80, . | 3.2 | 12 |
| 31 | Refractive index of Si-doped n-InGaAs. <i>Journal of Applied Physics</i> , 2008, 104, 073507. | 2.5 | 4 |
| 32 | Strong optical emissions from two-dimensional metal photonic crystals with semiconductor multiple quantum wells. <i>Journal of Applied Physics</i> , 2007, 101, 086107. | 2.5 | 0 |
| 33 | Growth of InGaSb Quantum Dot Structures on GaAs and Silicon Substrates. <i>Japanese Journal of Applied Physics</i> , 2007, 46, 2401-2404. | 1.5 | 15 |
| 34 | Large nitrogen composition of GaNSb grown by RF-MBE. <i>AIP Conference Proceedings</i> , 2007, , . | 0.4 | 0 |
| 35 | Nano-positioning of Sb-based semiconductor quantum structures for novel communications devices. <i>AIP Conference Proceedings</i> , 2007, , . | 0.4 | 0 |
| 36 | Site control of very low density InAs QDs on patterned GaAs nano-wire surfaces. <i>Journal of Crystal Growth</i> , 2007, 301-302, 846-848. | 1.5 | 3 |

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|----|--|-----|-----------|
| 37 | Metamorphic molecular beam epitaxy growth and selective wet etching for epitaxial layer lift-off of AlAsSb toward optical waveguides with high optical confinement. <i>Journal of Crystal Growth</i> , 2007, 301-302, 955-958. | 1.5 | 0 |
| 38 | (In)GaSb/AlGaSb quantum wells grown on Si substrates. <i>Thin Solid Films</i> , 2007, 515, 4467-4470. | 1.8 | 9 |
| 39 | Growth of antimonide compound semiconductor on Si(001) substrate. , 2006, , . | | 0 |
| 40 | Sb-based quantum dots for creating novel light-emitting devices for optical communications. , 2006, , . | | 4 |
| 41 | 1.51 $\frac{1}{4}$ μ m emission from InAs quantum dots with InGaAsSb strain-reducing layer grown on GaAs substrates. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2006, 32, 81-84. | 2.7 | 15 |
| 42 | Change in band configuration of quantum wells from type-II to type-I by increasing Sb composition x. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2006, 32, 230-233. | 2.7 | 3 |
| 43 | Optical communications waveband lasing from Sb-based quantum dot vertical-cavity laser. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2006, 32, 516-519. | 2.7 | 5 |
| 44 | Microwave induced Shubnikovâ€ˆde Hass-type oscillation in InGaAs/InAlAs heterostructures. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2006, 34, 393-396. | 2.7 | 0 |
| 45 | Residual carrier density in GaSb grown on Si substrates. <i>Thin Solid Films</i> , 2006, 515, 748-751. | 1.8 | 6 |
| 46 | Analysis of Novel Alignment Method for Fabricating Three-Dimensional Photonic Crystal. <i>Japanese Journal of Applied Physics</i> , 2006, 45, L135-L137. | 1.5 | 0 |
| 47 | Nanoscale structure fabrication of multiple AlGaSbâˆ•InGaSb quantum wells by reactive ion etching with chlorine-based gases toward photonic crystals. <i>Journal of Vacuum Science & Technology B</i> , 2006, 24, 2291. | 1.3 | 6 |
| 48 | Metamorphic InGaAs/AlAsSb quantum wells grown on GaAs substrates for intersubband devices operating toward short-wavelength region. <i>Electronics Letters</i> , 2006, 42, 600. | 1.0 | 1 |
| 49 | Selective Formation of Self-Organized InAs Quantum Dots Grown on Patterned GaAs Substrates by Molecular Beam Epitaxy. <i>Japanese Journal of Applied Physics</i> , 2006, 45, 3556-3559. | 1.5 | 1 |
| 50 | 1.55- $\hat{\mu}$ m-Waveband Emissions from Sb-Based Quantum-Dot Vertical-Cavity Surface-Emitting Laser Structures Fabricated on GaAs Substrate. <i>Japanese Journal of Applied Physics</i> , 2006, 45, 3423-3426. | 1.5 | 15 |
| 51 | Optical Cavity Properties of Metal Mirror Microcavities with InAsSb Quantum Dots. <i>Japanese Journal of Applied Physics</i> , 2006, 45, 8650-8652. | 1.5 | 1 |
| 52 | Initial growth stage of GaSb on Si(001) substrates with AlSb initiation layers. <i>Journal of Crystal Growth</i> , 2005, 283, 297-302. | 1.5 | 51 |
| 53 | Strong photoluminescence and laser operation of InAs quantum dots covered by a GaAsSb strain-reducing layer. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2005, 26, 395-399. | 2.7 | 25 |
| 54 | High-Quality GaSb/AlGaSb Quantum Well Grown on Si Substrate. <i>Japanese Journal of Applied Physics</i> , 2005, 44, L15-L17. | 1.5 | 18 |

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| 55 | Growth of InAsSb Quantum Dots on GaAs Substrates Using Periodic Supply Epitaxy. Japanese Journal of Applied Physics, 2005, 44, L696-L698. | 1.5 | 8 |
| 56 | All-optical control of the resonant-photon tunneling effect observed in GaAs δ -AlGaAs multilayered structures containing quantum dots. Applied Physics Letters, 2005, 87, 231119. | 3.3 | 10 |
| 57 | Over 1.3 μ m continuous-wave laser emission from InGaSb quantum-dot laser diode fabricated on GaAs substrates. Applied Physics Letters, 2005, 86, 203118. | 3.3 | 42 |
| 58 | Heteroepitaxial growth of GaSb on Si(001) substrates. Journal of Crystal Growth, 2004, 264, 21-25. | 1.5 | 106 |
| 59 | Growth of InAs Quantum Dots on a Low Lattice-Mismatched AlGaSb Layer Prepared on GaAs (001) Substrates. Solid State Phenomena, 2004, 99-100, 49-54. | 0.3 | 1 |
| 60 | Title is missing!. Journal of Superconductivity and Novel Magnetism, 2003, 16, 327-329. | 0.5 | 2 |
| 61 | Title is missing!. Journal of Superconductivity and Novel Magnetism, 2003, 16, 469-472. | 0.5 | 0 |
| 62 | Study for realization of spin-polarized field effect transistor in In _{0.75} Ga _{0.25} As/In _{0.75} Al _{0.25} As heterostructure. Physica E: Low-Dimensional Systems and Nanostructures, 2002, 12, 399-402. | 2.7 | 22 |
| 63 | Determination of Rashba spin splitting in In _x Ga _{1-x} As/In _y Al _{1-y} As by far-infrared magneto-optical absorption. Physica E: Low-Dimensional Systems and Nanostructures, 2002, 12, 432-434. | 2.7 | 9 |
| 64 | Spontaneous spin-splitting observed in resonant tunneling diode with narrow band-gap asymmetric quantum well. Physica E: Low-Dimensional Systems and Nanostructures, 2002, 13, 815-818. | 2.7 | 5 |
| 65 | Large spontaneous spin-splitting and enhanced effective g-factor in two-dimensional electron gases at In _{0.75} Ga _{0.25} As/In _{0.75} Al _{0.25} As metamorphic heterojunctions. Physica B: Condensed Matter, 2001, 298, 65-69. | 2.7 | 20 |
| 66 | An investigation of tunable spin-orbit interactions in front-gated In _{0.75} Ga _{0.25} As/In _{0.75} Al _{0.25} As heterojunctions. Physica E: Low-Dimensional Systems and Nanostructures, 2001, 10, 77-80. | 2.7 | 4 |
| 67 | Characterization of high indium content metamorphic InGaAs/InAlAs modulation-doped heterostructures. Journal of Crystal Growth, 2001, 227-228, 155-160. | 1.5 | 15 |
| 68 | Critical layer thickness study in In _{0.75} Ga _{0.25} As/In _{0.5} Al _{0.5} As pseudomorphic resonant tunneling diode structure grown on GaAs substrates. Journal of Crystal Growth, 2001, 227-228, 161-166. | 1.5 | 3 |
| 69 | Ballistic Spin Transport in Four-Terminal NiFe/In _{0.75} Ga _{0.25} As Structure. Japanese Journal of Applied Physics, 2001, 40, L1093-L1096. | 1.5 | 4 |
| 70 | Large spontaneous spin splitting in gate-controlled two-dimensional electron gases at normal In _{0.75} Ga _{0.25} As/In _{0.75} Al _{0.25} As heterojunctions. Journal of Applied Physics, 2001, 89, 8017-8021. | 2.5 | 183 |
| 71 | Large and anisotropic zero-field spin-splittings in In _x Ga _{1-x} As/In _y Al _{1-y} As (x,y>0.6) heterojunctions. Physica E: Low-Dimensional Systems and Nanostructures, 2000, 7, 992-996. | 2.7 | 6 |
| 72 | Possible large zero-field spin-splittings in In _x Ga _{1-x} As/In _y Al _{1-y} As (x,y=0.75) heterojunctions. Physica E: Low-Dimensional Systems and Nanostructures, 2000, 6, 771-774. | 2.7 | 6 |

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|----|--|-----|-----------|
| 73 | Spin-splitting transport in In _{0.75} Ga _{0.25} As/In _{0.75} Al _{0.25} As quantum wire field-effect-transistor. <i>Physica B: Condensed Matter</i> , 1999, 272, 114-116. | 2.7 | 22 |
| 74 | Dependencies of low-temperature electronic properties of MBE-grown GaAs/AlGaAs single heterojunctions upon arsenic species. <i>Journal of Crystal Growth</i> , 1999, 201-202, 800-804. | 1.5 | 0 |
| 75 | Very high electron mobilities at low temperatures in In _x Ga _{1-x} As/In _y Al _{1-y} As HEMTs grown lattice-mismatched on GaAs substrates. <i>Journal of Crystal Growth</i> , 1999, 201-202, 749-752. | 1.5 | 27 |
| 76 | Compensation mechanism of undoped GaAs films grown by molecular beam epitaxy using an As-valved cracker cell. <i>Applied Surface Science</i> , 1998, 130-132, 409-413. | 6.1 | 4 |
| 77 | Low Temperature High Electron Mobility in In _{0.75} Ga _{0.25} As/In _{0.75} Al _{0.25} As Modulation-Doped Hetrostructures Grown on GaAs Substrate. <i>Japanese Journal of Applied Physics</i> , 1998, 37, L1501-L1503. | 1.5 | 35 |
| 78 | Highly-Ordered and Highly-Stacked (150-Layer) Quantum Dots. , 0, , . | | 4 |
| 79 | Cross Phase Modulation Efficiency Enhancement in In _{0.8} Ga _{0.2} As/Al _{0.5} Ga _{0.5} As/Al _{0.56} Sb _{0.44} Coupled Double Quantum Wells by Tailoring Interband Transition Wavelength. <i>Applied Physics Express</i> , 0, 2, 042201. | 2.4 | 23 |
| 80 | Photoluminescence of an InSb layer on a Germanium substrate. <i>Semiconductor Science and Technology</i> , 0, , . | 2.0 | 0 |